# SK20GD065



# IGBT Module

## SK20GD065

**Preliminary Data** 

### **Features**

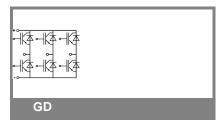
- Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL technology FWD
- · High short circuit capability
- Low tail current with low temperature dependence

## **Typical Applications\***

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

<b>Absolute Maximum Ratings</b> $T_s = 25  ^{\circ}\text{C}$ , unless otherwise specified					
Symbol	Conditions		Values	Units	
IGBT	•		•		
$V_{CES}$	T <sub>j</sub> = 25 °C		600	V	
I <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	24	Α	
		$T_s = 80  ^{\circ}C$	17	Α	
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		40	Α	
$V_{GES}$			± 20	٧	
t <sub>psc</sub>	$V_{CC}$ = 300 V; $V_{GE} \le 20$ V; $V_{CES} < 600$ V	T <sub>j</sub> = 125 °C	10	μs	
Inverse D	Piode		•		
I <sub>F</sub>	T <sub>j</sub> = 125 °C	$T_s = 25 ^{\circ}C$	22	Α	
		$T_s = 80  ^{\circ}C$	15	Α	
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		30	Α	
Module					
I <sub>t(RMS)</sub>				Α	
$T_{vj}$			-40 <b>+</b> 150	°C	
T <sub>stg</sub>			-40 <b>+</b> 125	°C	
V <sub>isol</sub>	AC, 1 min.		2500	V	

Characteristics $T_s =$		25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 0.5 \text{ mA}$		3	4	5	V
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = V <sub>CES</sub>	T <sub>j</sub> = 25 °C			0,07	mA
		T <sub>j</sub> = 125 °C				mA
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 20 V	T <sub>j</sub> = 25 °C			120	nA
		T <sub>j</sub> = 125 °C				nA
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1,2	1,3	V
		T <sub>j</sub> = 125 °C		1,1	0,9	V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		40		mΩ
		T <sub>j</sub> = 125°C		55		$m\Omega$
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 20 A, V <sub>GE</sub> = 15 V			2		V
		$T_j = 125^{\circ}C_{chiplev.}$		2,2		V
C <sub>ies</sub>				1,1		nF
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,11		nF
C <sub>res</sub>				0,063		nF
t <sub>d(on)</sub>		.,		36		ns
t <sub>r</sub> E <sub>on</sub>	$R_{Gon} = 30 \Omega$	V <sub>CC</sub> = 300V		30		ns
E <sub>on</sub>	$R_{Goff} = 30 \Omega$	I <sub>C</sub> = 20A T <sub>i</sub> = 125 °C		0,7 250		mJ
$t_{d(off)} \ t_{f}$	Goff - 30 32	V <sub>GE</sub> =±15V		60		ns ns
E <sub>off</sub>		GE -		0,4		mJ
R <sub>th(j-s)</sub>	per IGBT	· · · · · · · · · · · · · · · · · · ·			1,7	K/W



# **SK20GD065**



SEMITOP® 2

**IGBT** Module

SK20GD065

Preliminary Data

#### **Features**

- · Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- · CAL technology FWD
- · High short circuit capability
- Low tail current with low temperature dependence

### Typical Applications\*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

Characteristics								
Symbol	Conditions	İ	min.	typ.	max.	Units		
Inverse Diode								
$V_F = V_{EC}$	$I_{Fnom}$ = 20 A; $V_{GE}$ = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev</sub> .		1,6	1,9	V		
		T <sub>j</sub> = 125 °C <sub>chiplev.</sub>		1,9	1,9	V		
$V_{F0}$		T <sub>j</sub> = 25 °C		1	1,1	V		
		T <sub>j</sub> = 125 °C		0,9	1	V		
r <sub>F</sub>		T <sub>j</sub> = 25 °C		30	40	mΩ		
		T <sub>j</sub> = 125 °C		33	47	$m\Omega$		
I <sub>RRM</sub>	I <sub>F</sub> = 20 A	T <sub>i</sub> = 125 °C		27		Α		
$Q_{rr}$	di/dt = -1350 A/µs	,		2,3		μC		
E <sub>rr</sub>	V <sub>CC</sub> = 300V			0,4		mJ		
R <sub>th(j-s)D</sub>	per diode				2,3	K/W		
M <sub>s</sub>	to heat sink				2	Nm		
w			•	21		g		

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

